**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	40	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	5.4	Α
Static characte	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5.4 \text{ A}; T_j = 25 \text{ °C}$		-	23	30	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



**40 V N-channel Trench MOSFET** 

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate	0 	G G A A A A
4	S	source	TSOP6 (SOT457)	\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \
5	D	drain		
6	D	drain		s
				017aaa255

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMN30ENEA	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PMN30ENEA	3Q

**40 V N-channel Trench MOSFET** 

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	5.4	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	3.8	Α
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	22	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	667	mW
			[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode				1	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.6	Α
ESD maximu	um rating	,			1	
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche ru	uggedness	,	'	'	,	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 0.83 A; DUT in avalanche (unclamped)		-	16.7	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

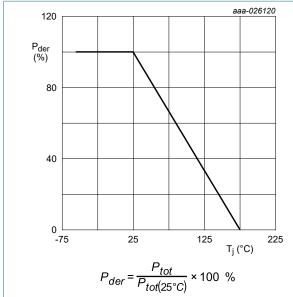
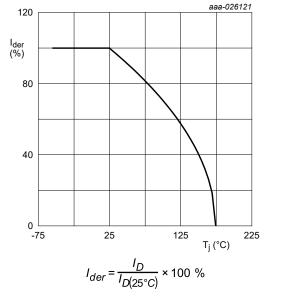


Fig. 1. Normalized total power dissipation as a function of junction temperature



ig. 2. Normalized continuous drain current as a function of junction temperature

### **40 V N-channel Trench MOSFET**

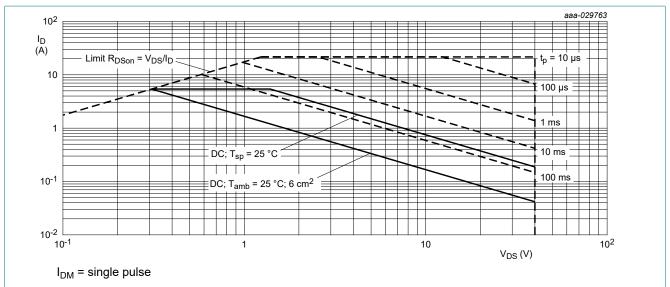


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

**40 V N-channel Trench MOSFET** 

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	195	225	K/W
junction t	junction to ambient	on to ambient	[2]	-	78	90	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

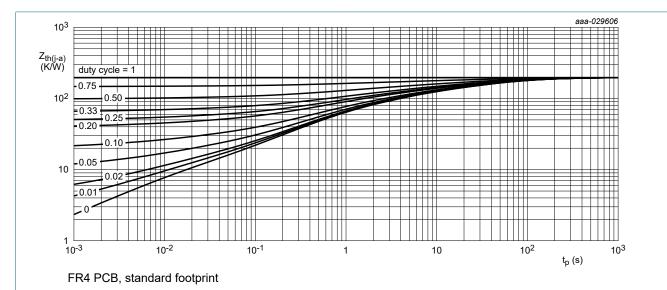
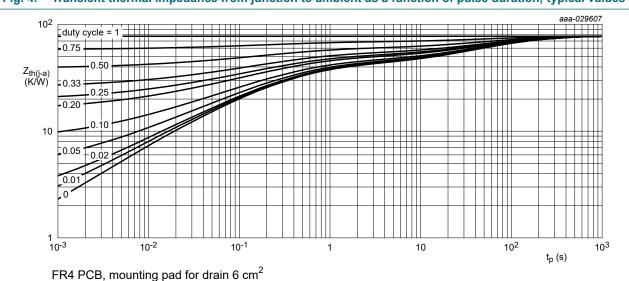


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



1114 1 OB, mounting pad for drain o on

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**40 V N-channel Trench MOSFET** 

# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.6	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μΑ
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5.4 A; T <sub>j</sub> = 25 °C	-	23	30	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5.4 A; T <sub>j</sub> = 175 °C	-	44	57	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 4.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	30	40	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	19	-	S
$R_G$	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics				'	
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 5 A; V <sub>GS</sub> = 10 V;	-	7.8	11.7	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.2	-	nC
$Q_{GD}$	gate-drain charge		-	1.6	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	440	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	76	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	39	-	pF
d(on)	turn-on delay time	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 5 A; V <sub>GS</sub> = 10 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	2	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	20	-	ns
t <sub>f</sub>	fall time		-	33	-	ns
Source-dra	in diode		'	,		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.6 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 1.6 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	11	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	4	-	nC

#### **40 V N-channel Trench MOSFET**

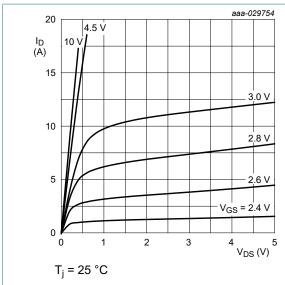


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

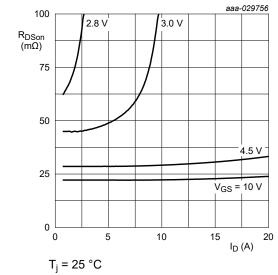


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

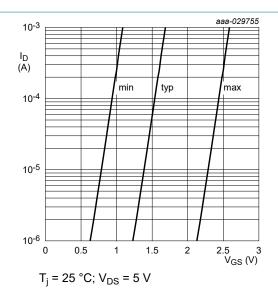


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

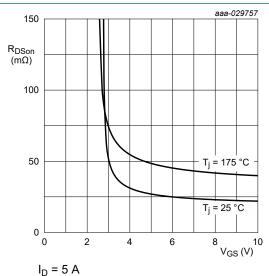


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

7/14

#### **40 V N-channel Trench MOSFET**

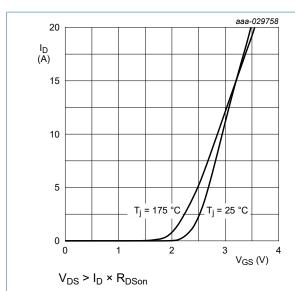


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

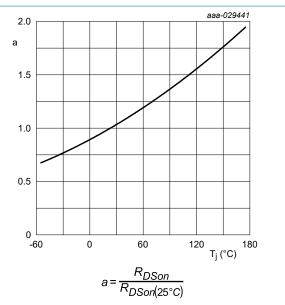


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

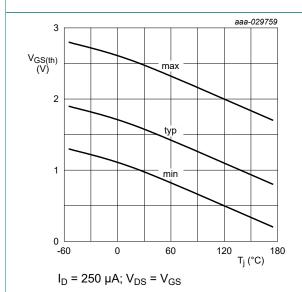


Fig. 12. Gate-source threshold voltage as a function of junction temperature

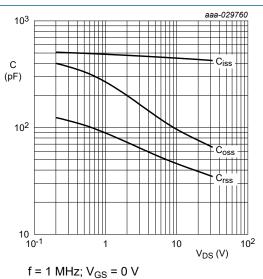


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

8 / 14

#### **40 V N-channel Trench MOSFET**

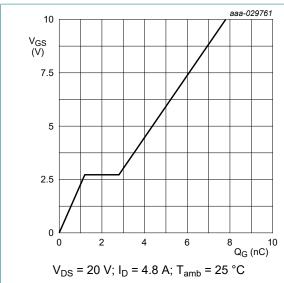


Fig. 14. Gate-source voltage as a function of gate charge; typical values

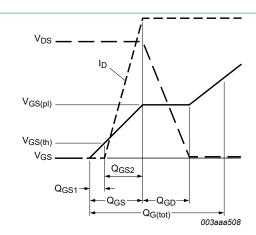


Fig. 15. Gate charge waveform definitions

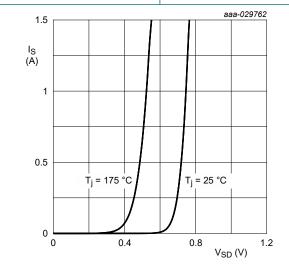


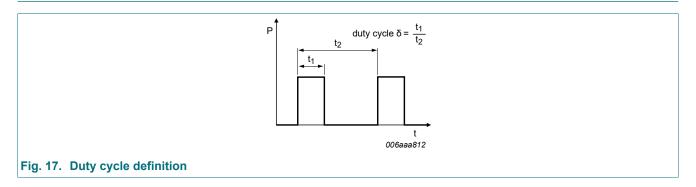
Fig. 16. Source current as a function of source-drain voltage; typical values

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 $V_{GS} = 0 V$ 

**40 V N-channel Trench MOSFET** 

## 11. Test information



## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### **40 V N-channel Trench MOSFET**

# 12. Package outline

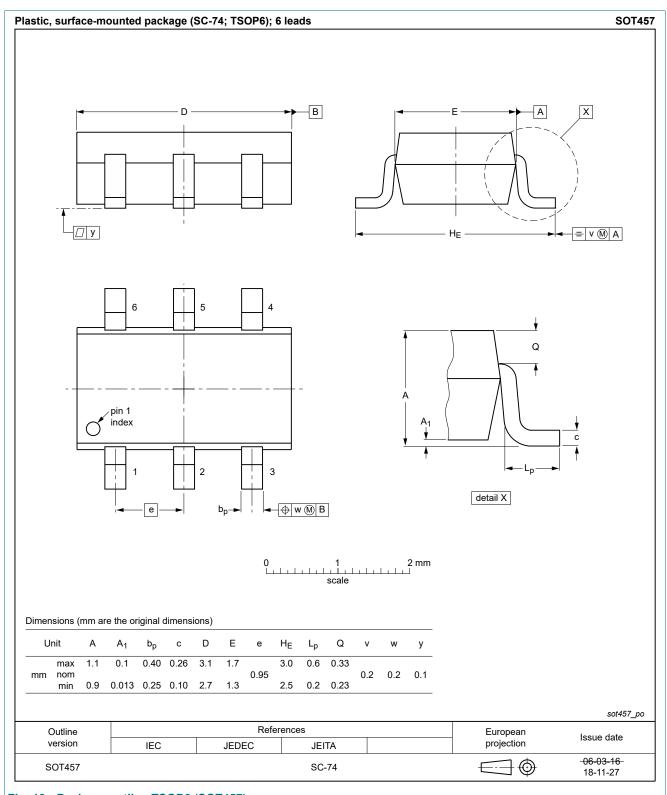


Fig. 18. Package outline TSOP6 (SOT457)

**40 V N-channel Trench MOSFET** 

# 13. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN30ENEA v.1	20190402	Product data sheet	-	-

#### 40 V N-channel Trench MOSFET

## 14. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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## **40 V N-channel Trench MOSFET**

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	5
10.	. Characteristics	6
11.	Test information	10
12.	Package outline	11
13.	. Revision history	.12
14.	Legal information	.13

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